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# N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY						
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)			
30	$0.0051 \text{ at V}_{GS} = 10 \text{ V}$	50 <sup>d</sup>	21.7			
30	$0.0063$ at $V_{GS} = 4.5 \text{ V}$	50 <sup>d</sup>	21.7			

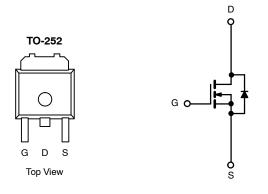
#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R<sub>q</sub> and UIS Tested
- Compliant to RoHS Directive 2002/95/EC





- Power Supply
  - Secondary Synchronous Rectification
- DC/DC Converter



N-Channel MOSFET

ABSOLUTE MAXIMUM RATING	$T_C = 25  ^{\circ}C$ , unless other	erwise noted			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V <sub>DS</sub>	30	V		
Gate-Source Voltage	V <sub>GS</sub>	± 20	- V		
Continuous Drain Current (T <sub>.I</sub> = 150 °C)	T <sub>C</sub> = 25 °C	1-	50 <sup>d</sup>		
Continuous Diairi Current (1) = 130 °C)	T <sub>C</sub> = 70 °C	I <sub>D</sub>	50 <sup>d</sup>	^	
Pulsed Drain Current		I <sub>DM</sub>	100	Α	
Avalanche Current		I <sub>AS</sub>	40		
Single Avalanche Energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	80	mJ	
	T <sub>C</sub> = 25 °C	В	59.5 <sup>b</sup>	W	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C <sup>c</sup>	$ P_D$	2.7		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Limit	Unit			
Junction-to-Ambient (PCB Mount) <sup>c</sup>	R <sub>thJA</sub>	46	°C/W			
Junction-to-Case (Drain)	R <sub>thJC</sub>	2.1	C/VV			

### Notes:

- a. Duty cycle  $\leq$  1 %.
- b. See SOA curve for voltage derating.c. When mounted on 1" square PCB (FR-4 material).
- d. Package limited.



<b>SPECIFICATIONS</b> T <sub>J</sub> = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{DS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			2.5 V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1		2.5		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 250	nA	
		V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V			1	μΑ	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$			50		
		V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 150 °C			250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	50			Α	
Drain-Source On-State Resistance <sup>a</sup>	В	$V_{GS} = 10 \text{ V}, I_D = 22 \text{ A}$		0.0042	0.0051	0	
Diain-Source On-State nesistance	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$		0.0052	0.0063	Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		110		S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			2780		pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 15 \text{ V}, f = 1 \text{ MHz}$		641			
Reverse Transfer Capacitance	C <sub>rss</sub>			260			
Total Gate Charge <sup>c</sup>	Qg	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$		44	66	nC	
Total date onlinge				21.7	32.6		
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 20 \text{ A}$		7			
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			6.7			
Gate Resistance	$R_{g}$	f = 1 MHz	0.4	2	4	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			8	16		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 15 \text{ V}, R_{L} = 1.5 \Omega$		9	18	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		35	53		
Fall Time <sup>c</sup>	t <sub>f</sub>			9	18		
Drain-Source Body Diode Ratings and Characteristics T <sub>C</sub> = 25 °C <sup>b</sup>							
Continuous Current	I <sub>S</sub>				50	Α	
Pulsed Current	I <sub>SM</sub>	SM			100	^	
Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V		0.75	1.5	V	
Reverse Recovery Time	t <sub>rr</sub>			34	51	ns	
Peak Reverse Recovery Current	I <sub>RM(REC)</sub>	I <sub>F</sub> = 10 A, dl/dt = 100 A/μs		2	3	Α	
Reverse Recovery Charge	Q <sub>rr</sub>			34	51	nC	

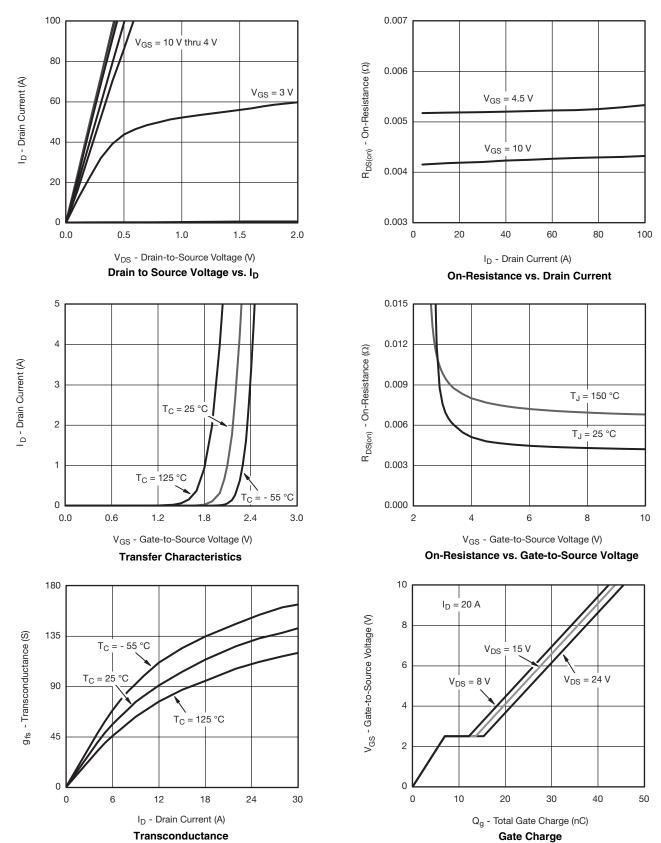
#### Notes:

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

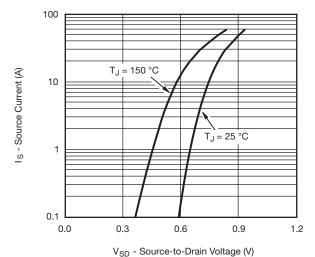


## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

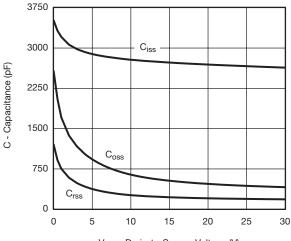




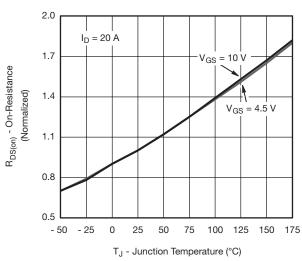
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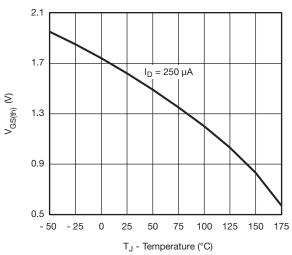
Source-Drain Diode Forward Voltage



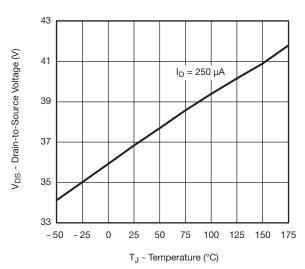
 $V_{DS}$  - Drain-to-Source Voltage (V)  $\label{eq:capacitance}$ 



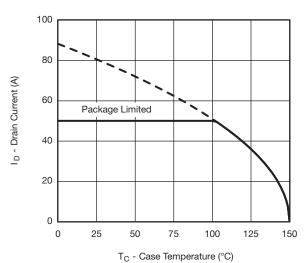
On-Resistance vs. Junction Temperature



Threshold Voltage



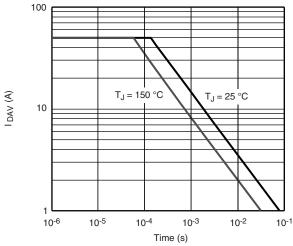
Drain Source Breakdown vs. Junction Temperature

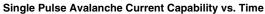


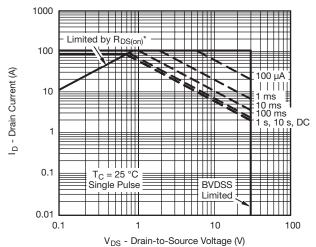
**Current Derating** 



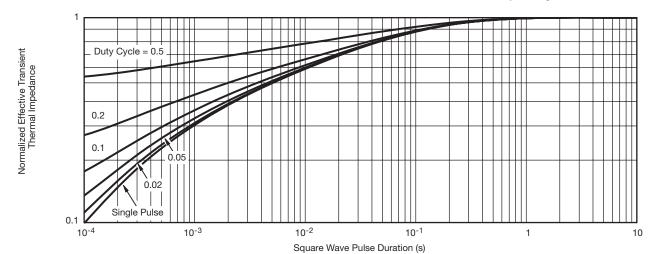
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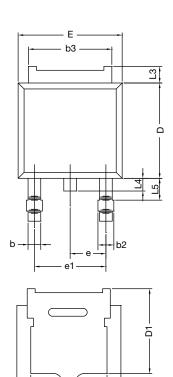
\*  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified **Safe Operating Area** 



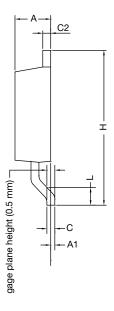
Normalized Thermal Transient Impedance, Junction-to-Case



# **TO-252AA CASE OUTLINE**



E1



	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	5.21	-	0.205	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	2.28 BSC		0.090 BSC	
e1	4.56	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	
ECN: X12-0247-Rev. M, 24-Dec-12					

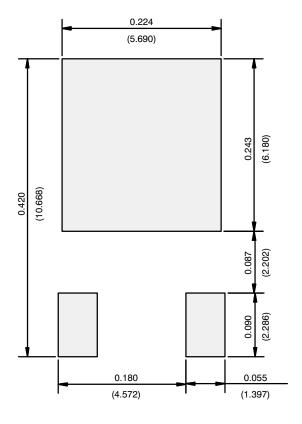
DWG: 5347

#### Note

• Dimension L3 is for reference only.



## **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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